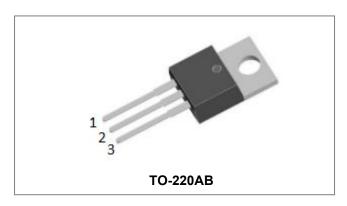






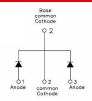
## MBR30100CTL SCHOTTKY RECTIFIER



#### **Features**

- 150°C T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- . All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Circuit Diagram**



#### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

## Maximum Ratings(limiting values, at 25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	100	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	Tc=126°C, In DC	15(Per Leg) 30(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	280	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 15A, Pulse, T <sub>J</sub> = 25 °C	0.75	0.80	V
	V <sub>F2</sub>	@ 15A, Pulse, T <sub>J</sub> = 125 °C	0.62	0.75	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	$@V_R = \text{rated } V_{R,} T_J = 25 ^{\circ}\text{C}$	0.002	1.00	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	2	40.0	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25 °C f_{SIG} = 1MHz$	623	800	pF
Series Inductance(Per Leg)	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •



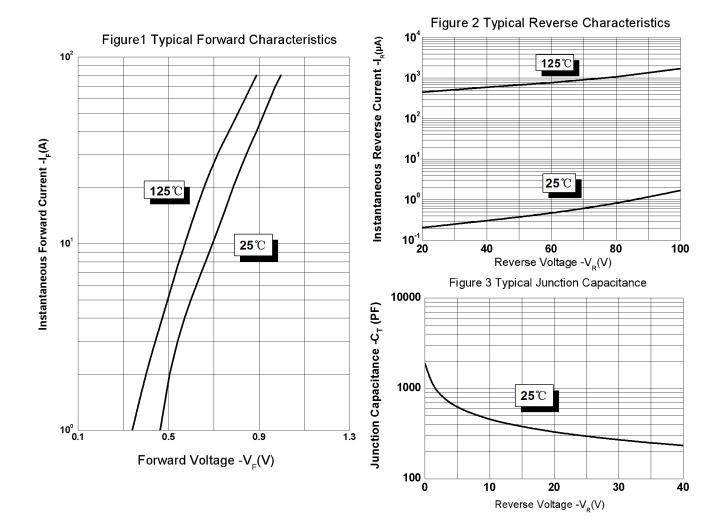




# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>0</sub> JC	DC operation	2	°C/W
Approximate Weight	wt	-	2	g

### **Ratings and Characteristics Curves**



<sup>•</sup> China - Germany - Korea - Singapore - United States •

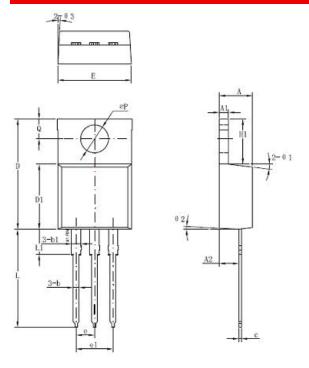
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •





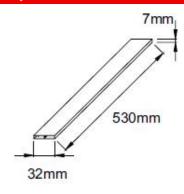


#### **Mechanical Dimensions TO-220AB**



Symbol	Dimensions in millimeters				
	Min	Typical	Max		
А	3.56	-	4.83		
A1	0.51	-	1.4		
A2	2.03	-	2.92		
b	0.38	-	1.02		
b1	1.14	-	1.78		
С	0.31	-	0.61		
D	14.22	-	16.51		
D1	8.38	-	9.42		
E	9.65	-	10.67		
е	-	2.54	-		
e1	-	5.08	-		
H1	5.84	-	6.86		
L	12.7	-	14.73		
L1	-	-	6.35		
ФР	-	3.56	-		
Q	2.54	-	3.43		

# **Tube Specification**



# **Marking Diagram**



Where XXXXX is YYWWL

 MBR
 = Device Type

 30
 = Forward Current (30A)

 100
 = Reverse Voltage(100V)

 CTL
 = Configuration

 SSG
 = SSG

 CTL
 = Configuration

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

#### **Ordering Information**

Device	Package	Shipping	
MBR30100CTL	TO-220AB (Pb-Free)	50 pcs/ tube	

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •







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